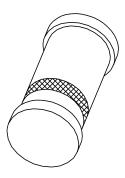
## DISCRETE SEMICONDUCTORS

## DATA SHEET



# **BZV55 series**Voltage regulator diodes

Product specification Supersedes data of November 1993 File under Discrete Semiconductors, SC01 1996 Apr 26





## **BZV55** series

#### **FEATURES**

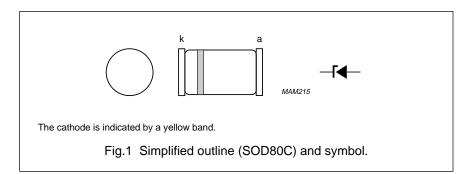
- Total power dissipation: max. 500 mW
- Three tolerance series: ±2%, ±3% and ±5%
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

#### **APPLICATIONS**

• Low-power voltage stabilizers or voltage references.

#### **DESCRIPTION**

Low-power voltage regulator diodes in small hermetically sealed glass SOD80C SMD packages. The diodes are available in the normalized E24  $\pm$ 2% (BZV55-B),  $\pm$ 3% (BZV55-F) and  $\pm$ 5% (BZV55-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V.



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>F</sub>	continuous forward current		_	250	mA
I <sub>ZSM</sub>	non-repetitive peak reverse current	$t_p$ = 100 μs; square wave; $T_j$ = 25 °C prior to surge		ables nd 2	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤50 °C; note 1	_	400	mW
		tie-point ≤50 °C; note 1	_	500	mW
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation	$t_p$ = 100 μs; square wave; $T_j$ = 25 °C prior to surge; see Fig.3	_	40	W
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		-65	+200	°C

2

### Note

1. Device mounted on a ceramic substrate of  $10 \times 10 \times 0.6$  mm.

## Voltage regulator diodes

BZV55 series

## **ELECTRICAL CHARACTERISTICS**

## Total BZV55-B, F and C series

 $T_j$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 mA; see Fig.4	0.9	V
I <sub>R</sub>	reverse current			
	BZV55-B/F/C2V4	V <sub>R</sub> = 1 V	50	μΑ
	BZV55-B/F/C2V7	V <sub>R</sub> = 1 V	20	μΑ
	BZV55-B/F/C3V0	V <sub>R</sub> = 1 V	10	μΑ
	BZV55-B/F/C3V3	V <sub>R</sub> = 1 V	5	μΑ
	BZV55-B/F/C3V6	V <sub>R</sub> = 1 V	5	μΑ
	BZV55-B/F/C3V9	V <sub>R</sub> = 1 V	3	μΑ
	BZV55-B/F/C4V3	V <sub>R</sub> = 1 V	3	μΑ
	BZV55-B/F/C4V7	V <sub>R</sub> = 2 V	3	μΑ
	BZV55-B/F/C5V1	V <sub>R</sub> = 2 V	2	μΑ
	BZV55-B/F/C5V6	V <sub>R</sub> = 2 V	1	μΑ
	BZV55-B/F/C6V2	V <sub>R</sub> = 4 V	3	μΑ
	BZV55-B/F/C6V8	$V_R = 4 V$	2	μΑ
	BZV55-B/F/C7V5	V <sub>R</sub> = 5 V	1	μΑ
	BZV55-B/F/C8V2	V <sub>R</sub> = 5 V	700	nA
	BZV55-B/F/C9V1	V <sub>R</sub> = 6 V	500	nA
	BZV55-B/F/C10	V <sub>R</sub> = 7 V	200	nA
	BZV55-B/F/C11	V <sub>R</sub> = 8 V	100	nA
	BZV55-B/F/C12	V <sub>R</sub> = 8 V	100	nA
	BZV55-B/F/C13	V <sub>R</sub> = 8 V	100	nA
	BZV55-B/F/C15 to 75	$V_R = 0.7V_{Znom}$	50	nA

BZV55 series

**Table 1** Per type BZV55-**B/F/C2V4** to **B/F/C24**  $T_j = 25$  °C; unless otherwise specified.

BZV55-B		×	ORKING V <sub>Z</sub> at I <sub>Ztest</sub>	WORKING VOLTAC $V_{Z}(V)$ at $I_{Ztest} = 5 \text{ mA}$	GE			DIFFERENTIAL RESISTANCE	ENTIAI TANCE (Ω)	_	TEN S.	TEMP. COEFF. $S_Z$ (mV/K) at $I_{Ztest} = 5 \text{ mA}$	EFF. mA	DIODE CAP. C <sub>d</sub> (pF) at f = 1 MHz;	NON-REPETITIVE PEAK REVERSE CURRENT
or F or C XXX	Tol. ±	Tol. ±2% (B)	Tol.	Tol. ±3% (F)	_	Tol. ±5% (C)	s  Ztest =	at I <sub>Ztest</sub> = 1 mA	a  Ztest =	at I <sub>Ztest</sub> = 5 mA	(see	(see Figs 5 and 6)	(9 pu	V <sub>R</sub> = 0 V	$_{ m LSM}$ (A) at $_{ m t_p}$ = 100 $_{ m LS}$ ; $_{ m T_{amb}}$ = 25 $^{\circ}$ C
	Ä	MAX.	MIN.	MAX.	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	Ν̈́	TYP.	MAX.	MAX.	MAX.
2V4	2.35	2.45	2.33	2.47	2.2	2.6	275	009	70	100	-3.5	9.1-	0	450	6.0
2V7	2.65	2.75	2.62	2.78	2.5	2.9	300	009	75	100	-3.5	-2.0	0	450	6.0
370	2.94	3.06	2.91	3.09	2.8	3.2	325	009	80	92	-3.5	-2.1	0	450	6.0
3V3	3.23	3.37	3.20	3.40	3.1	3.5	350	009	82	92	-3.5	-2.4	0	450	0.9
376	3.53	3.67	3.49	3.71	3.4	3.8	375	009	82	06	-3.5	-2.4	0	450	0.9
3/9	3.82	3.98	3.78	4.02	3.7	4.1	400	009	82	06	-3.5	-2.5	0	450	0.9
4V3	4.21	4.39	4.17	4.43	4.0	4.6	410	009	80	06	-3.5	-2.5	0	450	0.9
4V7	4.61	4.79	4.56	4.84	4.4	2.0	425	200	20	80	-3.5	-1.4	0.2	300	0'9
5V1	2.00	5.20	4.95	5.25	4.8	5.4	400	480	40	09	-2.7	-0.8	1.2	300	0'9
5V6	5.49	12'9	5.43	5.77	2'9	0.9	08	400	15	40	-2.0	1.2	2.5	300	0'9
6V2	80.9	6.32	6.01	6:39	8.3	9.9	40	150	9	10	0.4	2.3	3.7	200	0'9
8/9	99.9	6.94	6.60	7.00	6.4	7.2	30	80	9	15	1.2	3.0	4.5	200	0.9
7/15	7.35	29'2	7.28	7.72	0.7	6.7	30	80	9	15	2.5	4.0	5.3	150	4.0
8V2	8.04	98.36	7.95	8.45	2.7	8.7	40	80	9	15	3.2	4.6	6.2	150	4.0
9V1	8.92	9.28	8.83	9.37	8.5	9.6	40	100	9	15	3.8	5.5	7.0	150	3.0
10	9.80	10.20	9.70	10.30	9.4	10.6	20	150	8	20	4.5	6.4	8.0	06	3.0
11	10.80	11.20	10.67	11.33	10.4	11.6	09	150	10	20	5.4	7.4	9.0	85	2.5
12	11.80	12.20	11.64	12.36	11.4	12.7	20	150	10	25	0.9	8.4	10.0	85	2.5
13	12.70	13.30	12.61	13.39	12.4	14.1	20	170	10	30	7.0	9.4	11.0	80	2.5
15	14.70	15.30	14.55	15.45	13.8	15.6	20	200	10	30	9.2	11.4	13.0	75	2.0
16	15.70	16.30	15.50	16.50	15.3	17.1	20	200	10	40	10.4	12.4	14.0	75	1.5
18	17.60	18.40	17.50	18.50	16.8	19.1	20	225	10	45	12.4	14.4	16.0	70	1.5
20	19.60	20.40	19.40	20.60	18.8	21.2	60	225	15	55	14.4	16.4	18.0	09	1.5
22	21.60	22.40	21.30	22.70	20.8	23.3	60	250	20	55	16.4	18.4	20.0	60	1.25
24	23.50	24.50	23.30	24.70	22.8	25.6	9	250	25	70	18.4	20.4	22.0	55	1.25

BZV55 series

**Table 2** Per type BZV55-**B/F/C27** to **B/F/C75**  $T_j = 25 \, ^{\circ}C$ ; unless otherwise specified.

BZV55-B		M	WORKING VOLTA $V_{Z}(V)$ at $I_{Ztest} = 2 \text{ mA}$	RKING VOLTA $V_Z(V)$ at $I_{Ztest} = 2 mA$	GE			DIFFERENTIAL RESISTANCE r <sub>dif</sub> (\Oaksign)	ENTIAL ANCE Ω)		TEN S;	TEMP. COEFF. $S_{Z} (mV/K)$ at $I_{Ztest} = 2 \text{ mA}$	EFF. () mA	DIODE CAP.  C <sub>d</sub> (pF)  at f = 1 MHz;	NON-REPETITIVE PEAK REVERSE CURRENT
or F or C XXX	Tol. ±	Tol. ±2% (B)	Tol. ±	Tol. ±3% (F)	Tol. ±€	Tol. ±5% (C)	a  Ztest = 	at I <sub>Ztest</sub> = 0.5 m A	a Iztest =	at I <sub>Ztest</sub> = 2 mA	see F	(see Figs 5 and 6)	and 6)	V <sub>R</sub> = 0 V	$_{LSM}$ (A) at $t_{p}$ = 100 $\mu s$ ; $_{Tamb}$ = 25 $^{\circ}C$
	N N N	MAX.	N N	MAX.	Ä.	MAX.	TYP.	MAX.	TYP.	MAX.	z Z	TYP.	MAX.	MAX.	MAX.
27	26.50	27.50	26.20	27.80	25.1	28.9	65	300	25	80	21.4	23.4	25.3	50	1.0
30	29.40	30.60	29.10	30.90	28.0	32.0	20	300	30	80	24.4	26.6	29.4	50	1.0
33	32.30	33.70	32.00	34.00	31.0	35.0	75	325	35	80	27.4	29.7	33.4	45	6.0
36	35.30	36.70	34.90	37.10	34.0	38.0	80	350	35	06	30.4	33.0	37.4	45	8.0
36	38.20	39.80	37.80	40.20	37.0	41.0	80	320	40	130	33.4	36.4	41.2	45	2.0
43	42.10	43.90	41.70	44.30	40.0	46.0	85	375	45	150	37.6	41.2	46.6	40	9.0
47	46.10	47.90	45.60	48.40	44.0	50.0	85	375	20	170	42.0	46.1	51.8	40	0.5
51	50.00	52.00	49.50	52.50	48.0	54.0	06	400	09	180	46.6	51.0	57.2	40	0.4
99	54.90	57.10	54.30	57.70	52.0	0.09	100	425	20	200	52.2	57.0	63.8	40	6.0
62	08.09	63.20	60.10	63.90	58.0	0.99	120	450	80	215	58.8	64.4	71.6	35	6.0
89	09'99	69.40	00.99	70.00	64.0	72.0	150	475	06	240	9.59	71.7	79.8	35	0.25
75	73.50	76.50	72.80	77.20	70.0	79.0	170	200	92	255	73.4	80.2	9.88	35	0.2

## Voltage regulator diodes

BZV55 series

## THERMAL CHARACTERISTICS

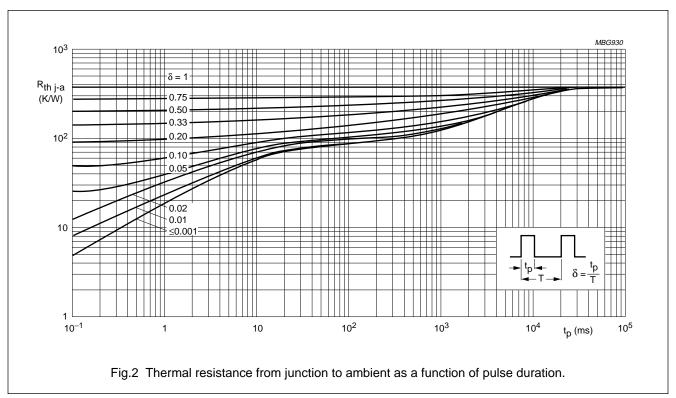
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		300	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	see Fig.2 and note 1	380	K/W

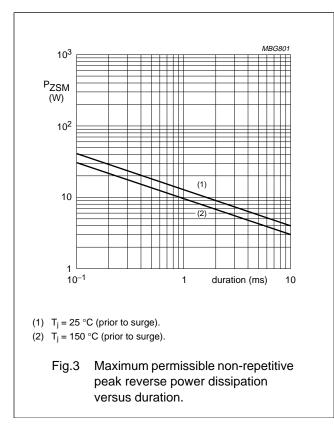
## Note

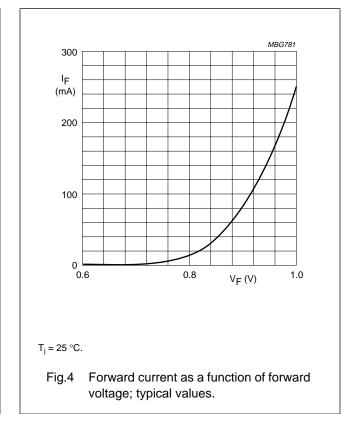
1. Device mounted on a ceramic substrate of  $10 \times 10 \times 0.6$  mm.

## BZV55 series

## **GRAPHICAL DATA**

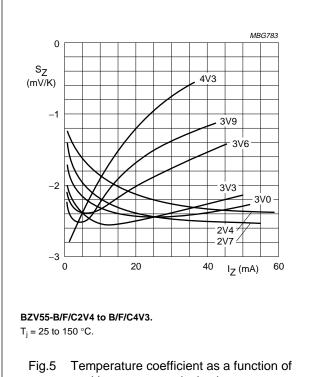






## Voltage regulator diodes

## BZV55 series



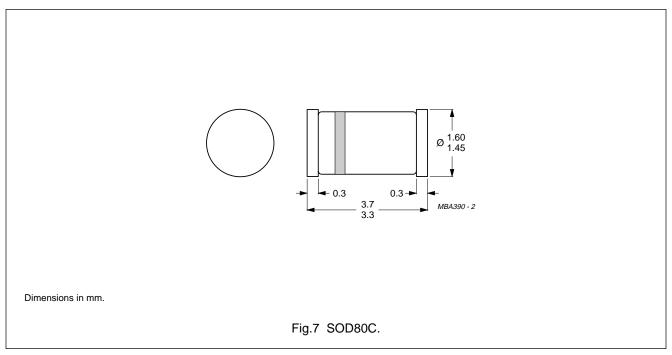
MBG782 10 S<sub>Z</sub> (mV/K) 11 10 9V1 5 8V2 7V5 6V8 6V2 5V6 5V1 0 4V7 12 16 <sub>IZ</sub> (mA) 20 BZV55-B/F/C4V7 to B/F/C12.  $T_i$  = 25 to 150 °C.

Fig.6 Temperature coefficient as a function of working current; typical values.

## Voltage regulator diodes

BZV55 series

#### **PACKAGE OUTLINE**



### **DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

#### Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.